

IN THE CLAIMS:

Please amend the following claims:

A1
Sub B1

1. A method of treating a chamber to at least partially remove residue from surfaces in the chamber, the method comprising [the steps of]:

- (a) providing an energized first process gas in the chamber to treat the surfaces in the chamber; and
- (b) providing an energized second process gas in the chamber to further treat the surfaces in the chamber, the second process gas being different than the first process gas.

A2
Sub B6

27. A method of etching a substrate in a chamber and at least partially removing [cleaning] etchant residue from surfaces in the chamber, the method comprising [the steps of]:

- (a) electrostatically holding the substrate in the chamber;
- (b) providing a first energized gas in the chamber, the first energized gas comprising an etchant [etching] gas to etch the substrate [and a residue cleaning gas]; and
- (c) providing a second energized gas in the chamber to at least partially remove [clean] etchant/residue from [deposited on] the surfaces in the chamber and simultaneously remove residual charge accumulated in the substrate.

Please add the following claims:

A3

46. A method according to claim 27 wherein the first energized gas further comprises an etchant residue cleaning gas.

Sub
B14

A3
cont

Sub
B11

Sub
B12

47. A method of etching a substrate in a chamber and at least partially removing etchant residue from surfaces in the chamber, the method comprising:

- (a) supporting the substrate in the chamber, the substrate having a layer thereon;
- (b) providing an energized gas in the chamber to etch through the layer;
- (c) after (b), providing an energized gas in the chamber to at least partially remove etchant residue from the surfaces in the chamber; and
- (d) after (c), removing the substrate from the chamber.

48. A method according to claim 47 wherein (b) comprises providing an energized gas comprising an etchant gas.

49. A method according to claim 47 wherein (c) comprises providing an energized gas comprising a cleaning gas.

50. A method according to claim 47 wherein (c) comprises removing residual charge accumulated in the substrate.

51. A method of etching a substrate in a chamber and at least partially removing etchant residue from surfaces in the chamber, the method comprising:

- (a) supporting the substrate in the chamber, the substrate having a first and a second layer thereon;
- (b) providing a first energized gas in the chamber to etch the first layer; and
- (c) providing a second energized gas in the chamber to etch the second layer and at least partially remove the etchant residue formed on the surfaces in the chamber in (b).

A3

~~37~~ 52. A method according to claim ~~51~~³⁶ wherein the second energized gas comprises carbon and fluorine species.

~~38~~ 53. A method according to claim ~~51~~³⁶ wherein the second energized gas comprises sulfur and fluorine species.

~~39~~ 54. A method according to claim ~~51~~³⁶ wherein the second energized gas comprises nitrogen and fluorine species.
